

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

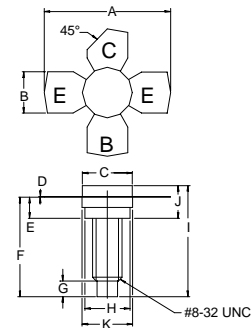
The **UML10** is Designed for High Power Class C Amplifier, in 225 to 400 MHz Military Communication Equipment.

**FEATURES:**

- Class C Operation
- $P_G = 10$  dB at 10 W/400 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.1 A
$V_{CB0}$	60 V
$V_{CEO}$	33 V
$V_{EBO}$	4.0 V
$P_{DISS}$	27 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	8.0 °C/W

**PACKAGE STYLE .280 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**ORDER CODE: ASI10694**
**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{EBO}$	$I_E = 20$ mA	4.0			V
$BV_{CES}$	$I_C = 20$ mA	33			V
$I_{CBO}$	$V_{CB} = 30$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 0.5$ A	25		80	---
$C_{OB}$	$V_{CB} = 28$ V $f = 860$ MHz			15	pF
$P_G$ $\eta_D$	$V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 400$ MHz	10	60		dB %